FDMS8D8N15C

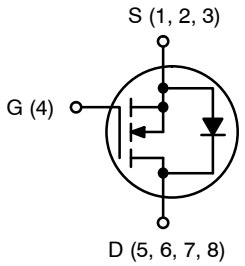
N-Channel Shielded Gate POWERTRENCH® MOSFET

150 V, 85 A, 8.8 mΩ

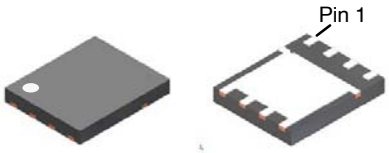
ON Semiconductor®

www.onsemi.com

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
150 V	8.8 mΩ @ 10 V	85 A
	9.4 mΩ @ 8 V	



N-CHANNEL MOSFET



Power 56
(PQFN8)
CASE 483AF

General Description

This N-Channel MV MOSFET is produced using ON Semiconductor's advanced PowerTrench process that incorporates Shielded Gate technology. This process has been optimized to minimize on−state resistance and yet maintain superior switching performance with best in class soft body diode.

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 8.8 mΩ at V_{GS} = 10 V, I_D = 45 A
- Max $r_{DS(on)}$ = 9.4 mΩ at V_{GS} = 8 V, I_D = 22.5 A
- Low Qrr, Soft Recovery Body Diode
- Lowers Switching Noise/EMI
- MSL1 Robust Package Design
- 100% UIL Tested
- These Devices are Pb−Free and are RoHS Compliant

Applications

- Primary DC−DC MOSFET
- Synchronous Rectifier in DC−DC and AC−DC
- Motor Drive
- Solar

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain−to−Source Voltage	150	V
V_{GS}	Gate−to−Source Voltage	±20	V
I_D	Drain Current: Continuous, T_C = 25°C (Note 5) Continuous, T_C = 100°C (Note 5) Continuous, T_A = 25°C (Note 1a) Pulsed (Note 4)	 85 54 12.2 340	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	102	mJ
P_D	Power Dissipation: T_C = 25°C T_A = 25°C (Note 1a)	 132 2.7	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case	0.95	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1a)	46	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain−to−Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	150			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C		86		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate−to−Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate−to−Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.5	3.5	4.5	V
$\Delta V_{GS(th)}/\Delta T_J$	Gate−to−Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C		−7.9		mV/°C
$r_{DS(on)}$	Static Drain−to−Source On Resistance	V_{GS} = 10 V, I_D = 45 A		7.0	8.8	mΩ
		V_{GS} = 8 V, I_D = 22.5 A		7.6	9.4	
		V_{GS} = 10 V, I_D = 45 A, T_J = 125°C		12.8	16.1	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 45 A		120	216	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 75 V, V_{GS} = 0 V, f = 1 MHz		3132	3600	pF
C_{oss}	Output Capacitance			927	1160	pF
C_{rss}	Reverse Transfer Capacitance			5.3	9.3	pF
R_g	Gate Resistance			0.73	1.2	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 75 V, I_D = 45 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		23	40	ns
t_r	Rise Time			19	38	ns
$t_{d(off)}$	Turn-Off Delay Time			30	49	ns
t_f	Fall Time			5	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V, V_{DD} = 75 V, I_D = 45 A		38	50	nC
Q_{gs}	Gate−to−Source Charge	V_{DD} = 75 V, I_D = 45 A		16.4		nC
Q_{gd}	Gate−to−Drain “Miller” Charge	V_{DD} = 75 V, I_D = 45 A		5.7		nC
Q_{oss}	Output Charge	V_{DD} = 75 V, V_{GS} = 0 V		101		nC

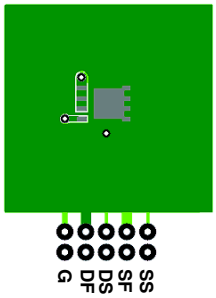
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source−to−Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.2 A (Note 2)		0.73	0.98	V
		V_{GS} = 0 V, I_S = 45 A (Note 2)		0.88	1.0	
t_{rr}	Reverse Recovery Time	I_F = 45 A, di/dt = 100 A/μs		68	86	ns
Q_{rr}	Reverse Recovery Charge			108	172	nC
t_{rr}	Reverse Recovery Time	I_F = 45 A, di/dt = 1000 A/μs		39	50	ns
Q_{rr}	Reverse Recovery Charge			495	748	nC

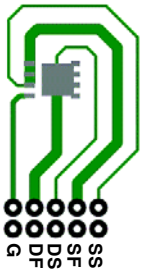
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta CA}$ is determined by the user's board design.



a) 46°C/W when mounted on a 1 in^2 pad of 2 oz copper.



b) 115°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E_{AS} of 102 mJ is based on starting T_J = 25°C; N-ch: L = 0.1 mH, I_{AS} = 45 A, V_{DD} = 150 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} = 45 A.
4. Pulsed Id please refer to Figure 11 SOA graph for more details. (Note: the final number may change pending results on device characterization).
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

PACKAGE MARKING AND ORDERING INFORMATION

Device	Marking	Package	Reel Size	Tape Width	Quantity
FDMS8D8N15C	FDMS8D8N15C	Power 56 (PQFN8) (Pb-Free / Halogen Free)	13″	12 mm	3000 units

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted.)

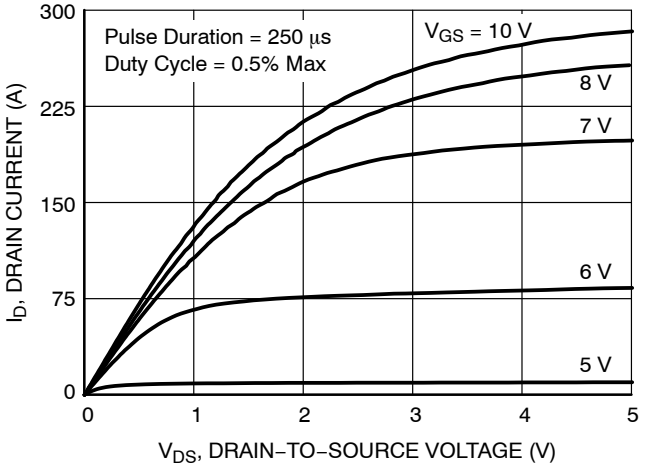


Figure 1. On−Region Characteristics

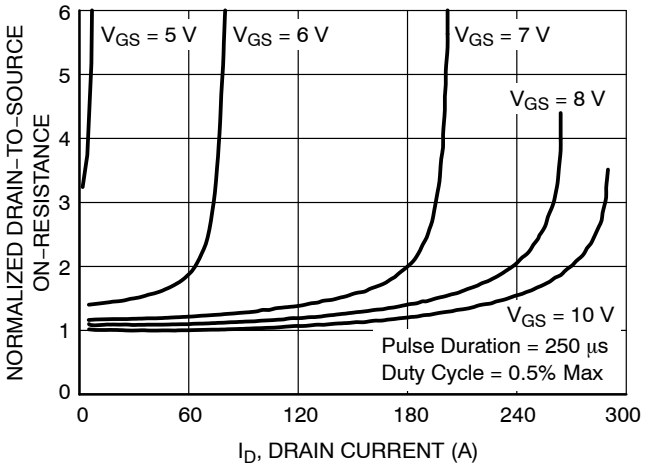


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

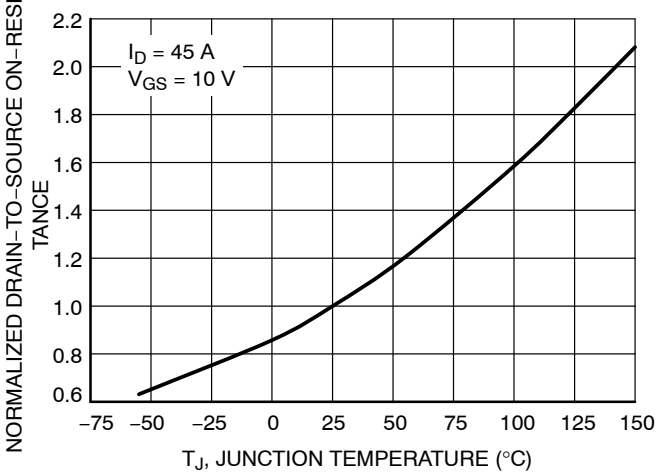


Figure 3. Normalized On−Resistance vs. Junction Temperature

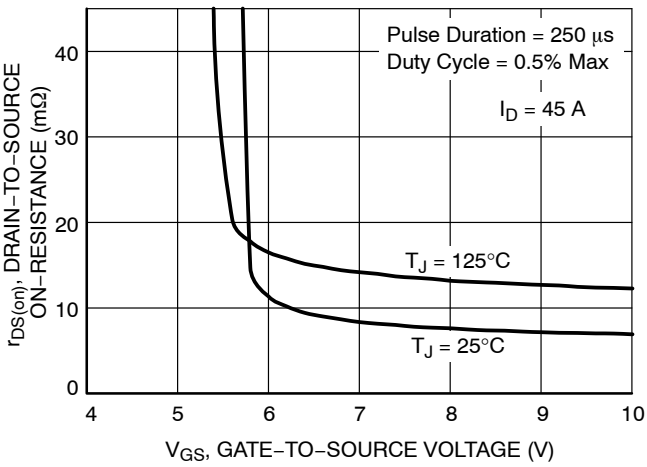


Figure 4. On−Resistance vs. Gate−to−Source Voltage

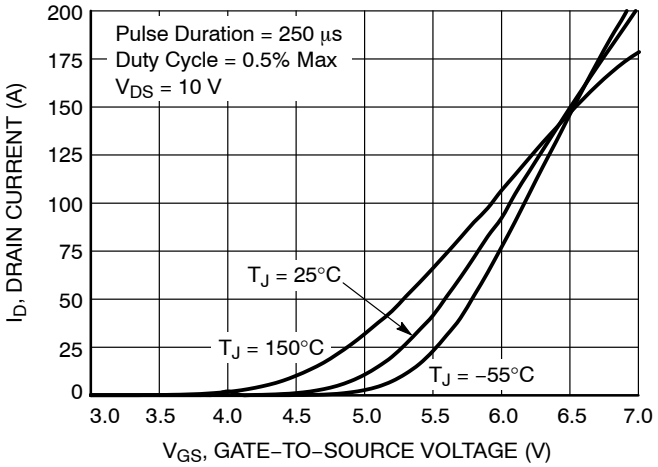


Figure 5. Transfer Characteristics

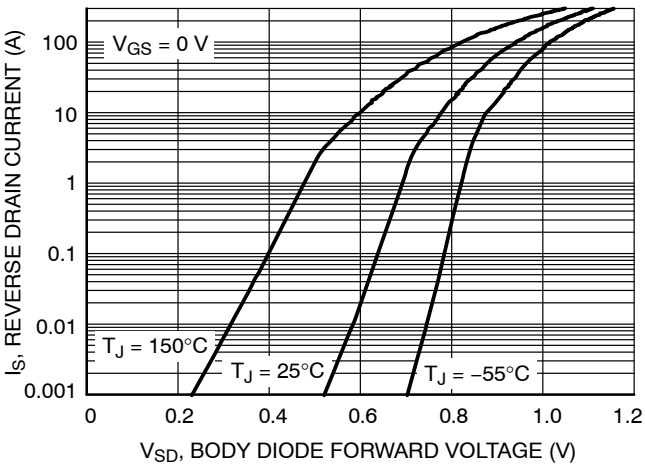


Figure 6. Source−to−Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted.)

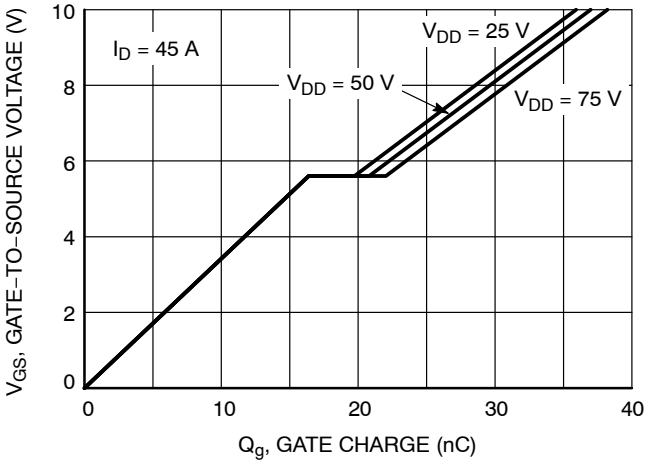


Figure 7. Gate Charge Characteristics

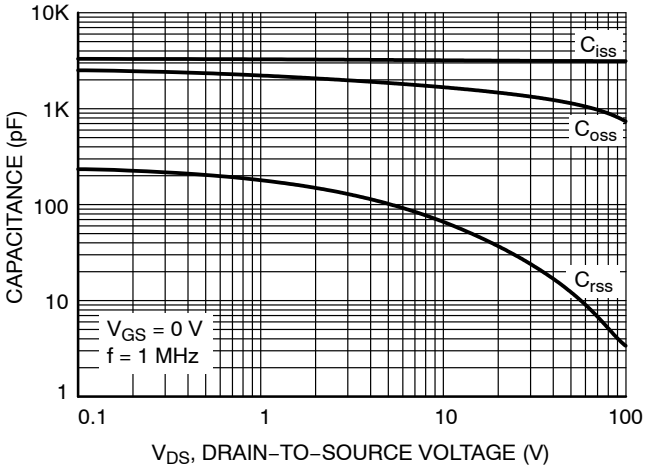


Figure 8. Capacitance vs. Drain−to−Source Voltage

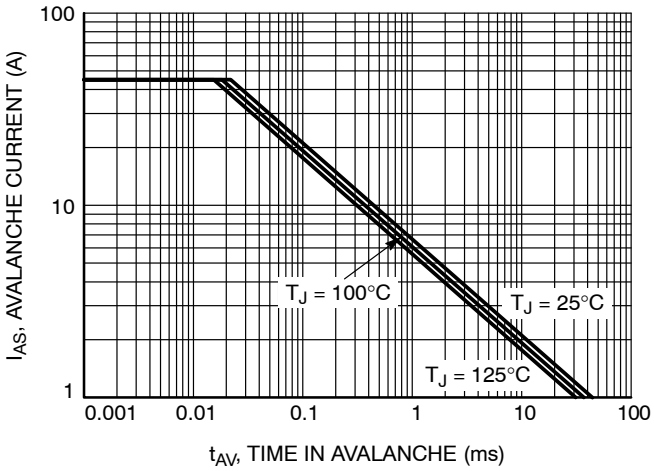


Figure 9. Unclamped Inductive Switching Capability

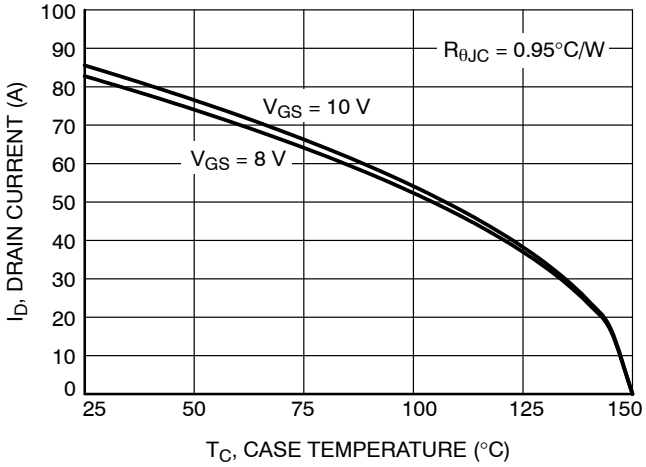


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

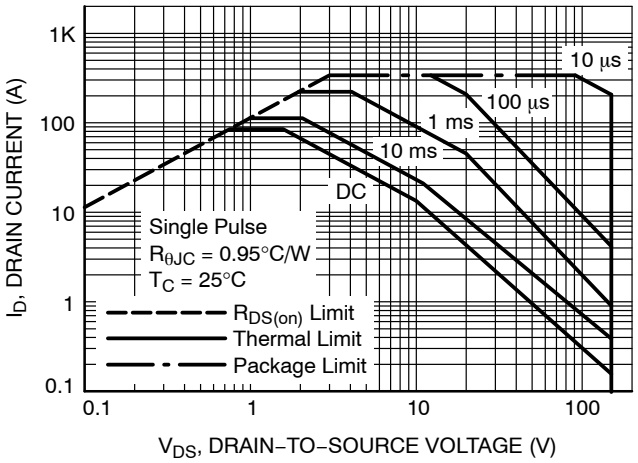


Figure 11. Forward Bias Safe Operating Area

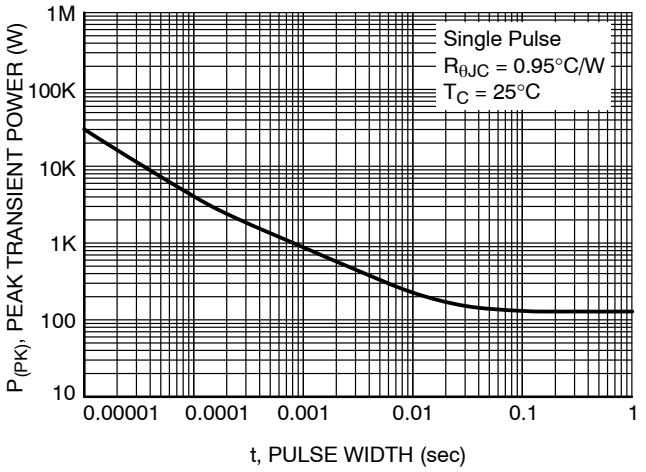


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted.)

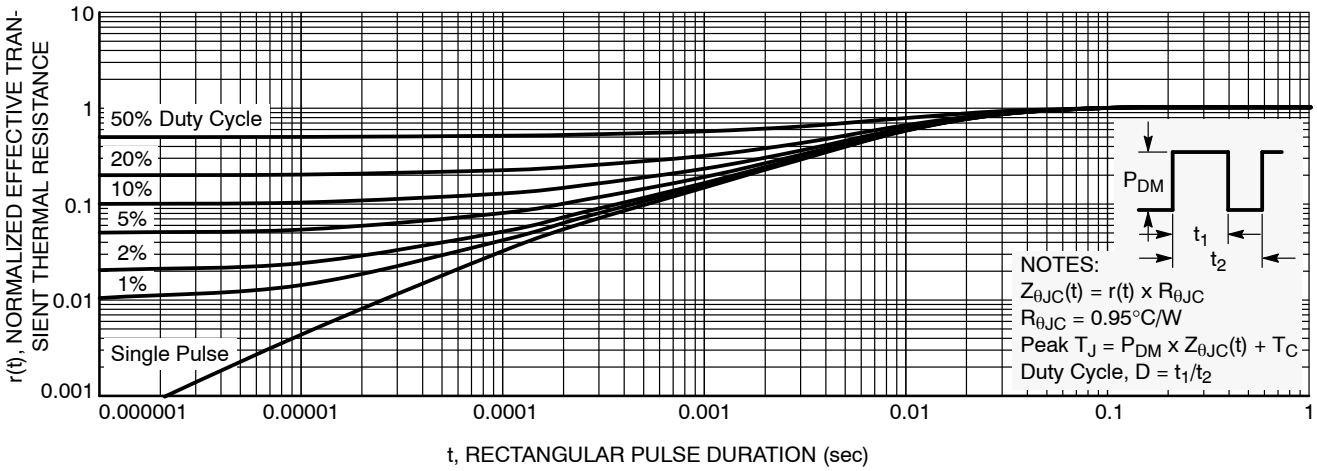
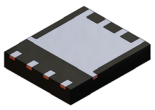
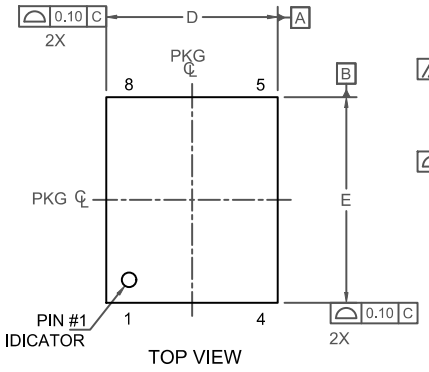


Figure 13. Junction−to−Case Transient Thermal Response Curve

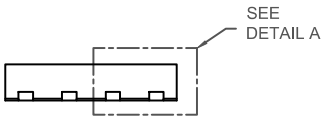


PQFN8 5X6, 1.27P
CASE 483AF
ISSUE A

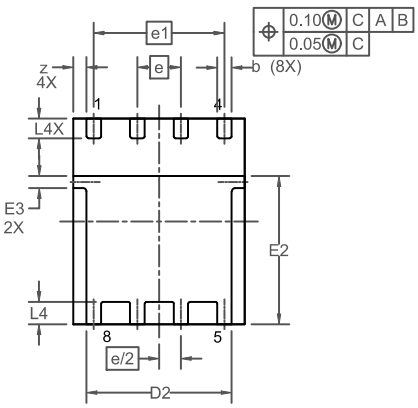
DATE 06 JUL 2021



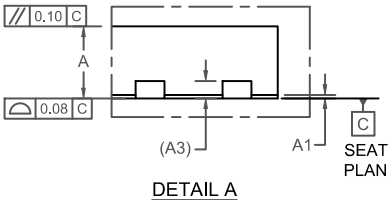
TOP VIEW



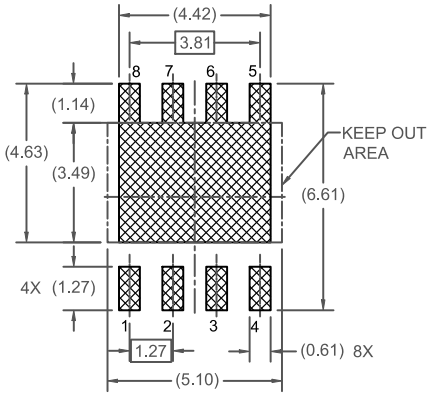
SIDE VIEW



BOTTOM VIEW



DETAIL A
SCALE: 2:1



LAND PATTERN
RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES: UNLESS OTHERWISE SPECIFIED

A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
E) IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	-	0.05
A3	0.20 REF.		
b	0.37	0.42	0.47
D	4.90	5.00	5.10
D2	4.13	4.23	4.33
E	5.90	6.00	6.10
E2	4.23	4.33	4.43
E3	0.35 REF.		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
L	0.52	0.57	0.62
L4	0.55	0.65	0.75
z	0.38 REF		

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DESCRIPTION:	**PQFN8 5X6, 1.27P**	**PAGE 1 OF 1**

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